

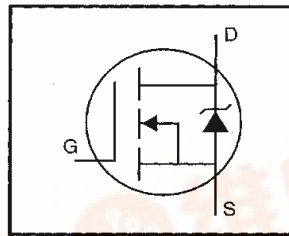
# International IR Rectifier

PD - 95626

## IRF624PbF

### HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead-Free



$$V_{DSS} = 250V$$

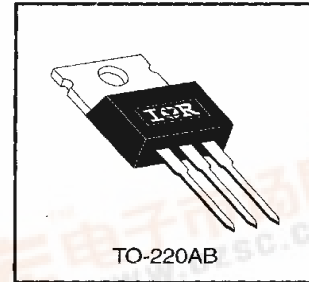
$$R_{DS(on)} = 1.1\Omega$$

$$I_D = 4.4A$$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



### Absolute Maximum Ratings

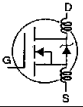
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	4.4	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	2.8	
$I_{DM}$	Pulsed Drain Current ①	14	
$P_D @ T_C = 25^\circ C$	Power Dissipation	50	W
	Linear Derating Factor	0.40	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	100	mJ
$I_{AR}$	Avalanche Current ①	4.4	A
$E_{AR}$	Repetitive Avalanche Energy ①	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.8	V/ns
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting Torque, 6-32 or M3 screw	10 lbf·in (1.1 N·m)	

### Thermal Resistance

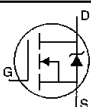
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	2.5	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	



## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

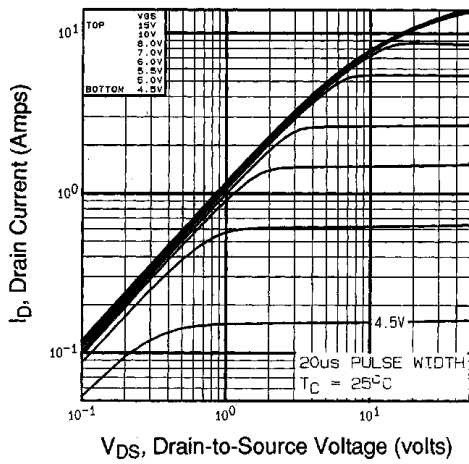
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	250	—	—	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.36	—	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	1.1	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =2.6A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	—	4.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA
g <sub>fs</sub>	Forward Transconductance	1.5	—	—	S	V <sub>DS</sub> =50V, I <sub>D</sub> =2.6A ④
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> =250V, V <sub>GS</sub> =0V
		—	—	250		V <sub>DS</sub> =200V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> =20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> =-20V
Q <sub>g</sub>	Total Gate Charge	—	—	14	nC	I <sub>D</sub> =4.4A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	2.7		V <sub>DS</sub> =200V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	7.8		V <sub>GS</sub> =10V See Fig. 6 and 13 ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	7.0	—	ns	V <sub>DD</sub> =125V
t <sub>r</sub>	Rise Time	—	13	—		I <sub>D</sub> =4.4A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	20	—		R <sub>G</sub> =18Ω
t <sub>f</sub>	Fall Time	—	12	—		R <sub>D</sub> =28Ω See Figure 10 ④
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	260	—	pF	V <sub>GS</sub> =0V
C <sub>oss</sub>	Output Capacitance	—	77	—		V <sub>DS</sub> =25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	15	—		f=1.0MHz See Figure 5

## Source-Drain Ratings and Characteristics

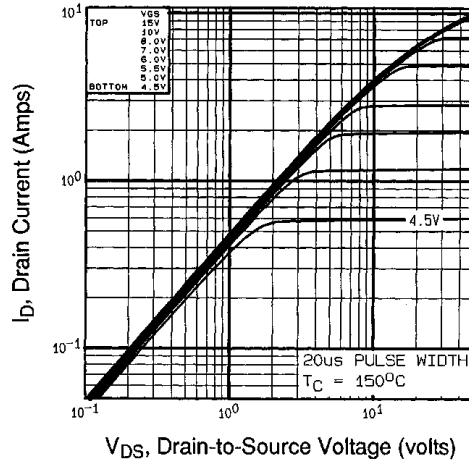
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	4.4	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	14		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.8	V	T <sub>J</sub> =25°C, I <sub>S</sub> =4.4A, V <sub>GS</sub> =0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	200	400	ns	T <sub>J</sub> =25°C, I <sub>F</sub> =4.4A
Q <sub>rr</sub>	Reverse Recovery Charge	—	0.93	1.9	μC	di/dt=100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

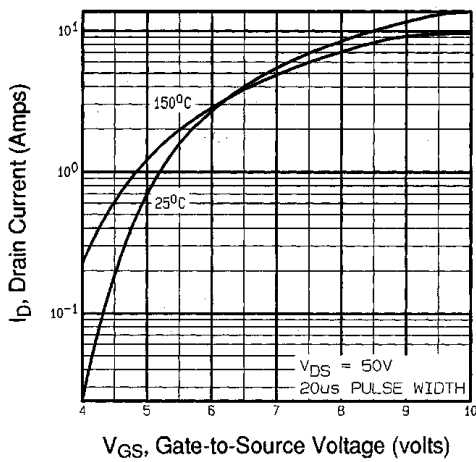
- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② V<sub>DD</sub>=50V, starting T<sub>J</sub>=25°C, L=8.3mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=4.4A (See Figure 12)
- ③ I<sub>SD</sub>≤4.4A, di/dt≤90A/μs, V<sub>DD</sub>≤V<sub>(BR)DSS</sub>, T<sub>J</sub>≤150°C
- ④ Pulse width ≤ 300 μs; duty cycle ≤2%.



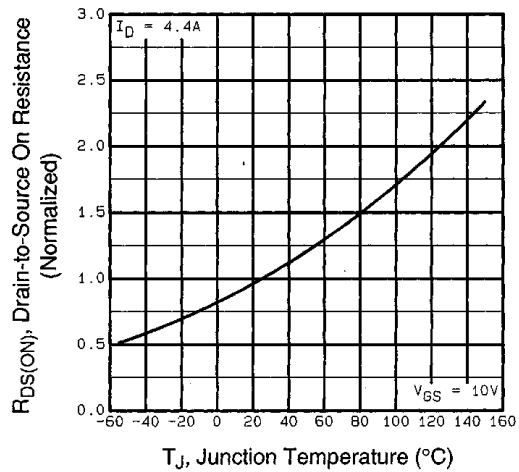
**Fig 1.** Typical Output Characteristics,  
 $T_C=25^\circ\text{C}$



**Fig 2.** Typical Output Characteristics,  
 $T_C=150^\circ\text{C}$



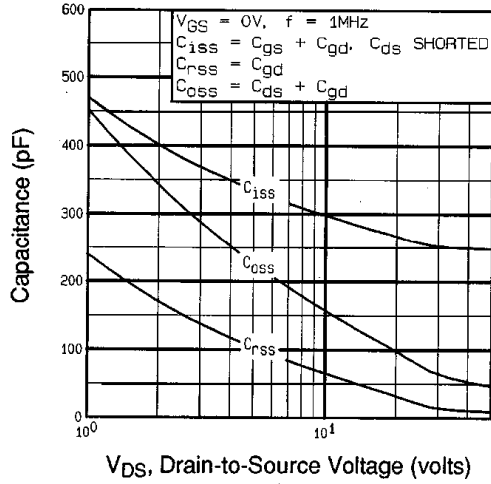
**Fig 3.** Typical Transfer Characteristics



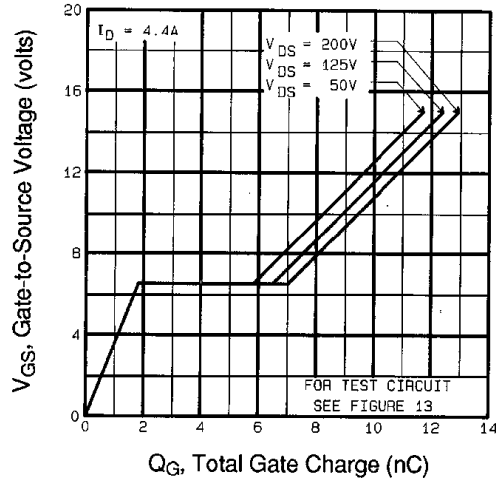
**Fig 4.** Normalized On-Resistance  
 Vs. Temperature

# IRF624PbF

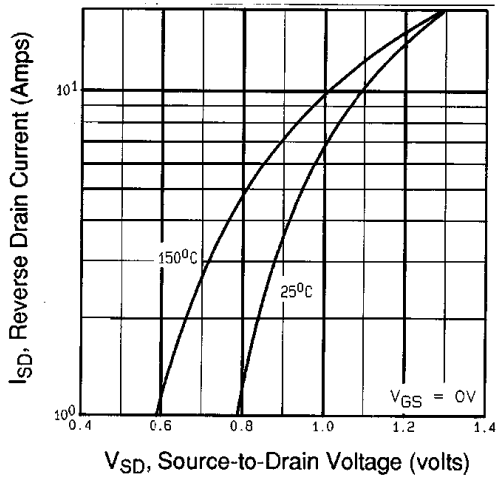
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**IR** Rectifier



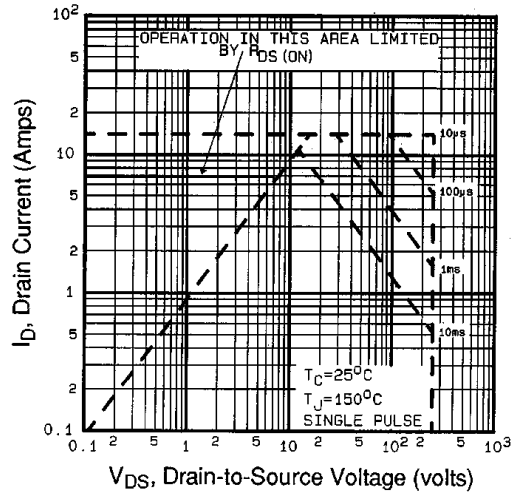
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



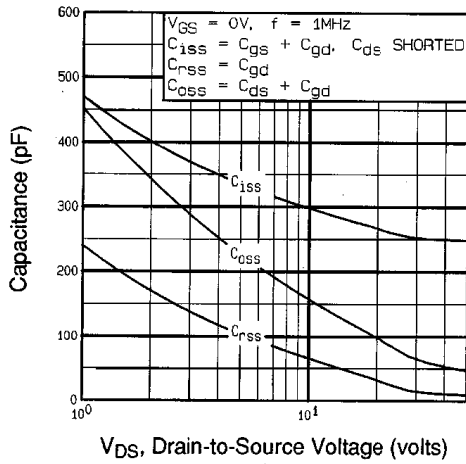
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



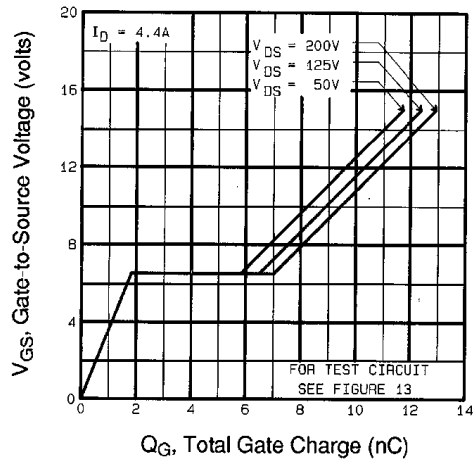
**Fig 7.** Typical Source-Drain Diode Forward Voltage



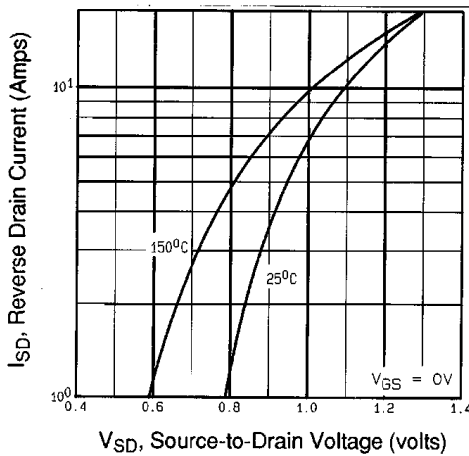
**Fig 8.** Maximum Safe Operating Area



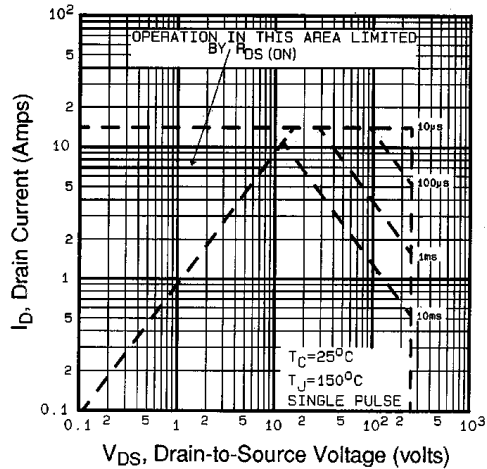
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



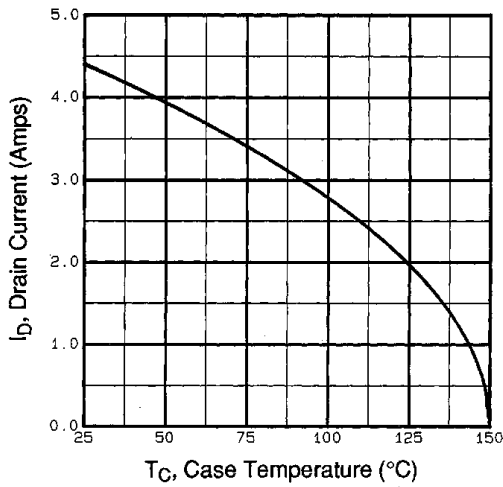
**Fig 7.** Typical Source-Drain Diode Forward Voltage



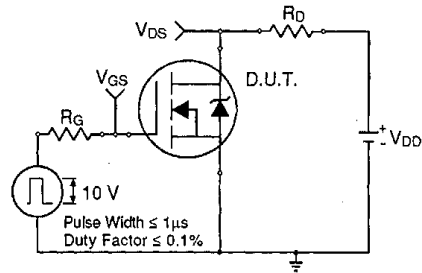
**Fig 8.** Maximum Safe Operating Area

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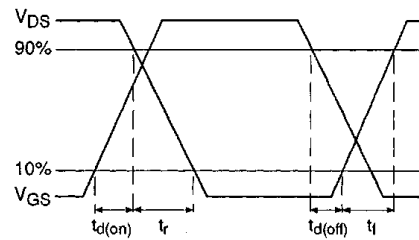
International  
**IR** Rectifier



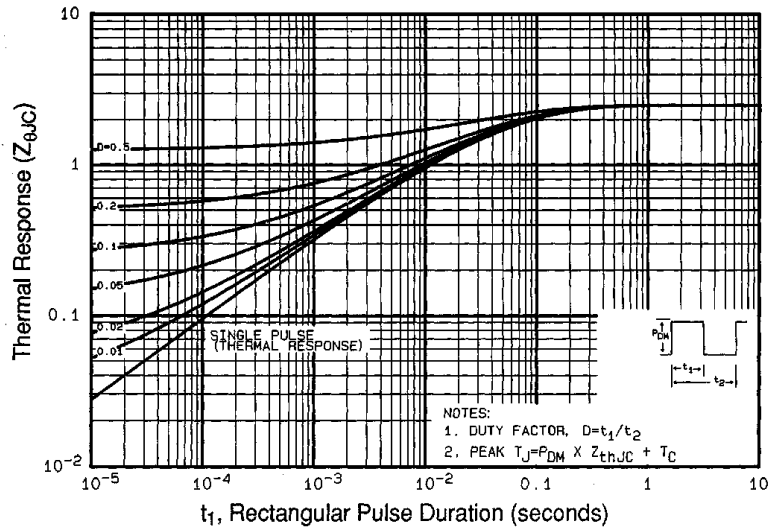
**Fig 9.** Maximum Drain Current Vs. Case Temperature



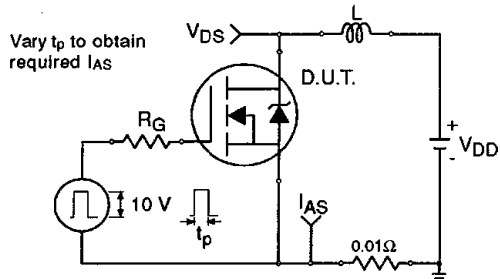
**Fig 10a.** Switching Time Test Circuit



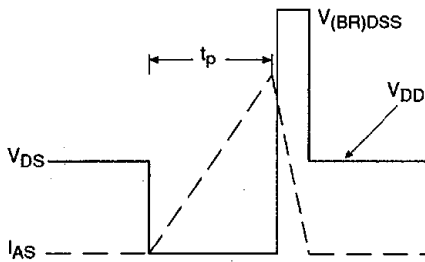
**Fig 10b.** Switching Time Waveforms



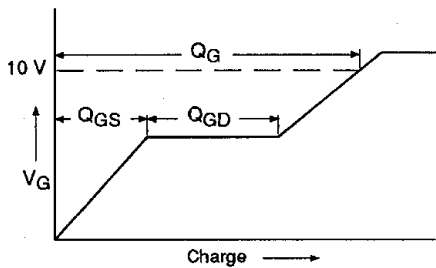
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



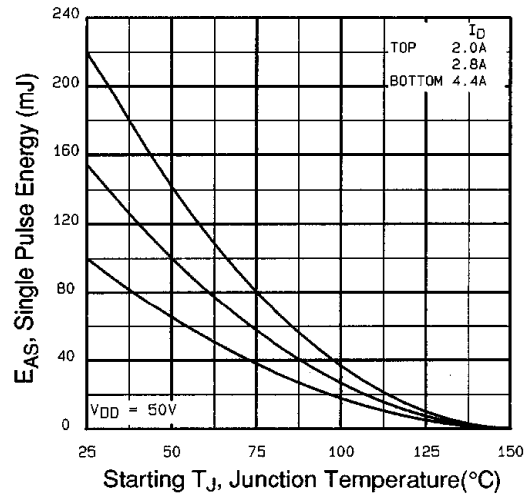
**Fig 12a. Unclamped Inductive Test Circuit**



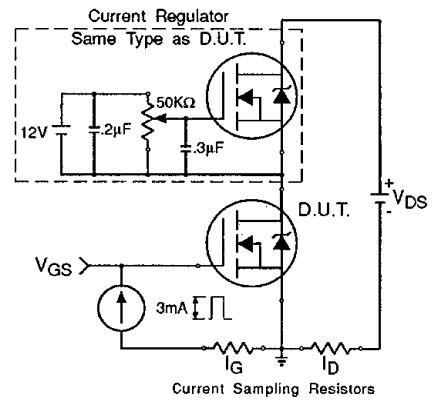
**Fig 12b. Unclamped Inductive Waveforms**



**Fig 13a. Basic Gate Charge Waveform**

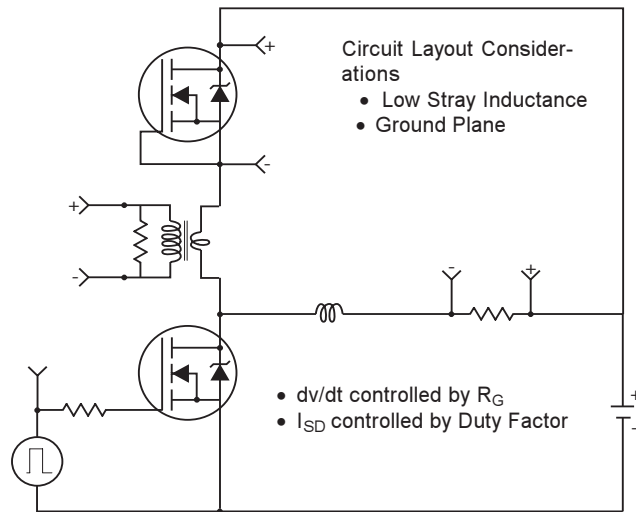


**Fig 12c. Maximum Avalanche Energy Vs. Drain Current**

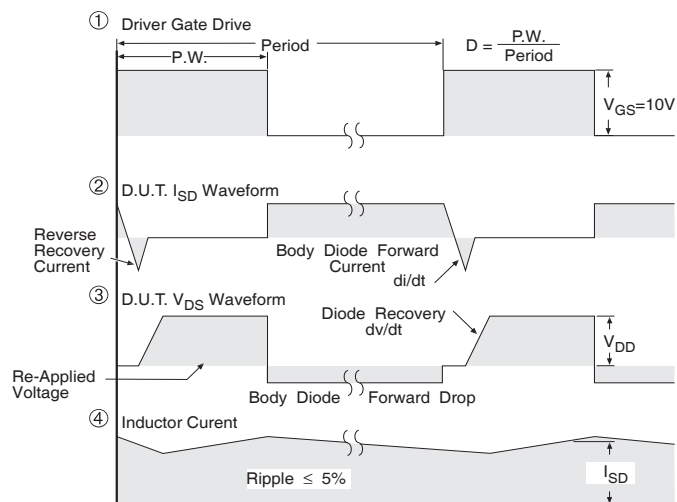


**Fig 13b. Gate Charge Test Circuit**

## Peak Diode Recovery dv/dt Test



\* Reverse Polarity for P-Channel



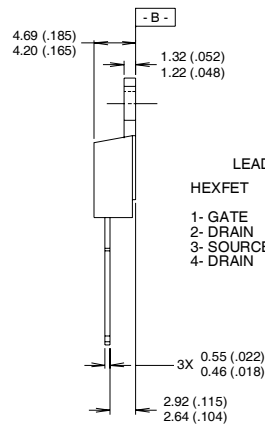
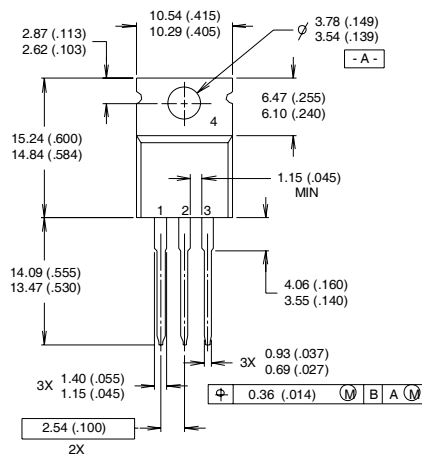
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig. 14** For N and P Channel HEXFETS



## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



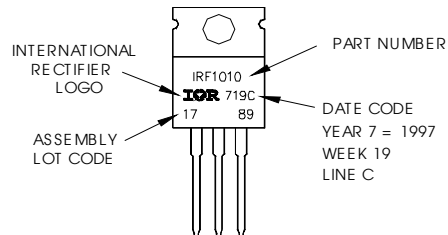
LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK
1- GATE	1- GATE
2- DRAIN	2- COLLECTOR
3- SOURCE	3- EMITTER
4- DRAIN	4- COLLECTOR

- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
  - 2 CONTROLLING DIMENSION : INCH
  - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
  - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
 position indicates "Lead-Free"



Data and specifications subject to change without notice.